# Switch-mode Power Rectifier 45 V, 30 A

# MBR30L45CTG, MBRF30L45CTG

### **Features and Benefits**

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 150°C Operating Junction Temperature
- 30 A Total (15 A Per Diode Leg)
- Guard-Ring for Stress Protection

### **Applications**

- Power Supply Output Rectification
- Power Management
- Instrumentation

#### **Mechanical Characteristics:**

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes 260°C Max. for 10 Seconds
- Shipped 50 Units Per Plastic Tube
- This is a Pb–Free Device\*

# **MAXIMUM RATINGS**

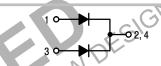
Please See the Table on the Following Page



# ON Semiconductor®

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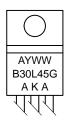
# DUAL SCHOTTKY BARRIER RECTIFIERS 30 AMPERES, 45 VOLTS



### MARKING DIAGRAMS

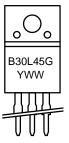


TO-220 CASE 221A PLASTIC





TO-220 FULLPAK™ CASE 221D



B30L45 = Device Code A = Assembly Location

Y = Year
WW = Work Week
AKA = Polarity Designator
G = Pb-Free Device

## **ORDERING INFORMATION**

Device	Package	Shipping
MBR30L45CTG	TO-220 (Pb-Free)	50 Units/Rail
MBRF30L45CTG	TO-220FP (Pb-Free)	50 Units/Rail

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<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### MAXIMUM RATINGS (Per Diode Leg)

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	45	V
Average Rectified Forward Current (Rated $V_R$ ) $T_C = 137$ °C		I <sub>F(AV)</sub>	15	А
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz)		I <sub>FRM</sub>	30	Α
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave,	single phase, 60 Hz)	I <sub>FSM</sub>	190	Α
Operating Junction Temperature (Note 1)		TJ	-55 to +150	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C
Voltage Rate of Change (Rated V <sub>R</sub> )		dv/dt	10,000	V/μs
ESD Ratings: Machine Model = C Human Body Model = 3B			> 400 > 8000	V
THERMAL CHARACTERISTICS			JES.	-
Maximum Thermal Resistance (MBR30L45CTG)	Junction-to-Case Junction-to-Ambient	$\begin{array}{c} R_{\theta JC} \\ R_{\theta JA} \end{array}$	1.9 45	°C/W
(MBRF30L45CTG)	Junction-to-Case	R <sub>θ</sub> JC	2.2	

# **ELECTRICAL CHARACTERISTICS** (Per Diode Leg)

Maximum Instantaneous Forward Voltage (Note 2) $ \begin{aligned} &(I_F=15~A,T_C=25^\circ\text{C})\\ &(I_F=15~A,T_C=125^\circ\text{C})\\ &(I_F=30~A,T_C=25^\circ\text{C})\\ &(I_F=30~A,T_C=25^\circ\text{C})\\ &(I_F=30~A,T_C=125^\circ\text{C}) \end{aligned} $	ORMAT	0.50 0.44 0.61 0.60	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, T <sub>C</sub> = 25°C) (Rated DC Voltage, T <sub>C</sub> = 125°C)	i <sub>R</sub>	0.65 250	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction–to–Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

2. Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle <2.0%.

## **TYPICAL CHARACTERISTICS**

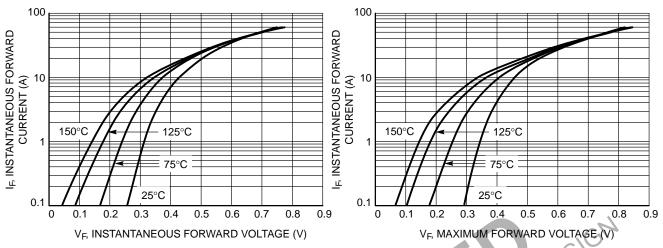


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

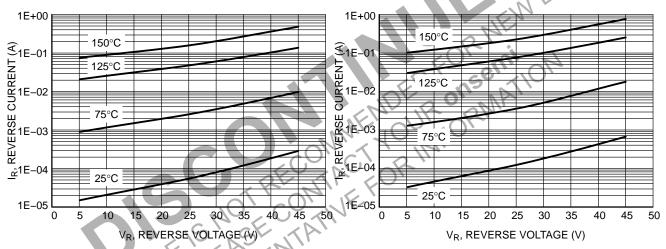


Figure 3. Typical Reverse Current

**Figure 4. Maximum Reverse Current** 

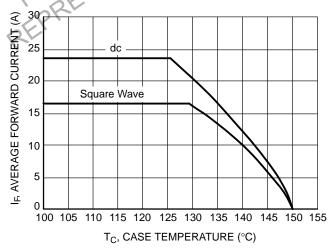


Figure 5. Current Derating

#### **TYPICAL CHARACTERISTICS**

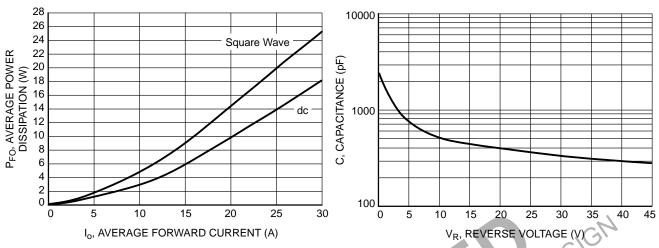


Figure 6. Forward Power Dissipation

Figure 7. Typical Capacitance

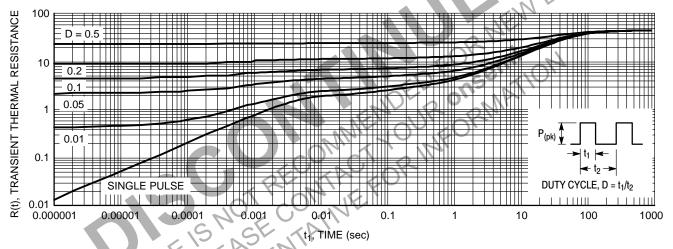


Figure 8. Thermal Response Junction-to-Ambient for MBR30L45CTG

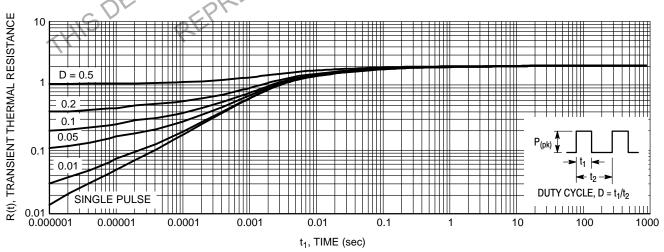
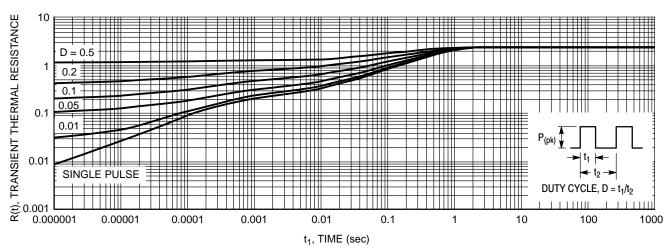


Figure 9. Thermal Response Junction-to-Case for MBR30L45CTG



CONNENDED FOR NEW DESIGN

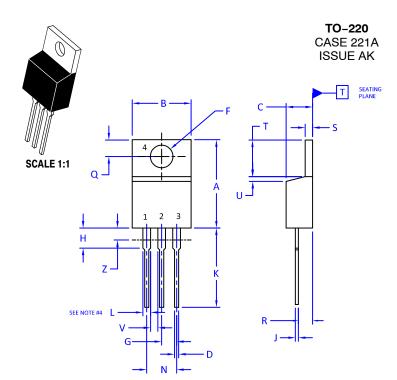
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**DATE 13 JAN 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

#### 4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	COLLECTOR	STYLE 3: PIN 1. 2. 3. 4.	ANODE	2. 3.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	STYLE 6: PIN 1. 2. 3. 4.	CATHODE ANODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.			GATE SOURCE DRAIN	STYLE 11: PIN 1. 2. 3. 4.		STYLE 12: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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# **MECHANICAL CASE OUTLINE**





SCALE 1:1

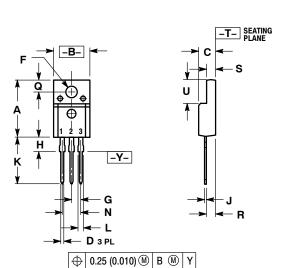
## TO-220 FULLPAK CASE 221D-03 ISSUE K

**DATE 27 FEB 2009** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116 0.129		2.95	3.28
G	0.100 BSC		2.54 BSC	
Н	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200	BSC	5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88



# **MARKING DIAGRAMS**

STYLE 1: PIN 1. GATE 2. DRAIN 3. SOURCE

STYLE 4: PIN 1. CATHODE

3. CATHODE

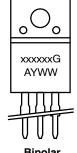
ANODE

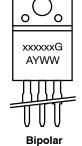
STYLE 2: PIN 1. BASE 2. COLLECTOR 3. EMITTER 2.

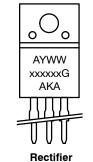
STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE

STYLE 3: PIN 1. ANODE

CATHODE
 ANODE







= Assembly Location xxxxxx = Specific Device Code G = Pb-Free Package Υ = Year

= Assembly Location WW = Work Week = Year XXXXXX = Device Code = Work Week = Pb-Free Package WW G AKA = Polarity Designator

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